



General Description

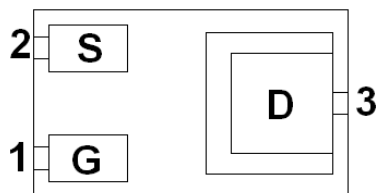
AFN1602E, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer, and low in-line power loss are needed in commercial industrial surface mount applications.

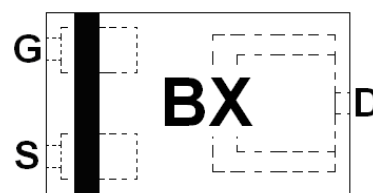
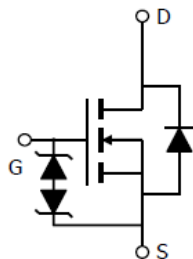
Features

- $I_D=0.8A, R_{DS(ON)}=360m\Omega@V_{GS}=4.5V$
- $I_D=0.7A, R_{DS(ON)}=420m\Omega@V_{GS}=2.5V$
- $I_D=0.5A, R_{DS(ON)}=560m\Omega@V_{GS}=1.8V$
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation
- ESD Protected
- DFN1.0X0.6-3L package design

Pin Description (DFN1.0X0.6-3L)



BOTTOM VIEW



TOP VIEW

Application

- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Smart Phones, Pagers

Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN1602EFN106RG	BX	DFN1.0X0.6-3L	Tape & Reel	10000 EA

※ B Product Code

※ X Monthly Code

(even year : A, B~ L)

(odd year : M, N~X)

※ AFN1602EFN106RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	0.7
		T _A =70°C	0.4
Pulsed Drain Current	I _{DM}	1.0	A
Continuous Source Current(Diode Conduction)	I _S	0.3	A
Power Dissipation	P _D	T _A =25°C	0.27
		T _A =70°C	0.16
Operating Junction Temperature	T _J	-55/150	°C
Storage Temperature Range	T _{STG}	-55/150	°C

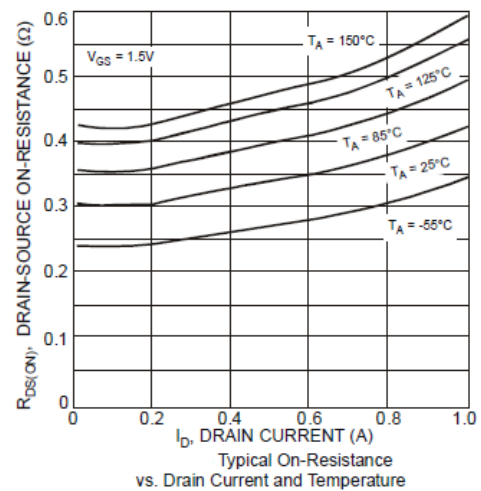
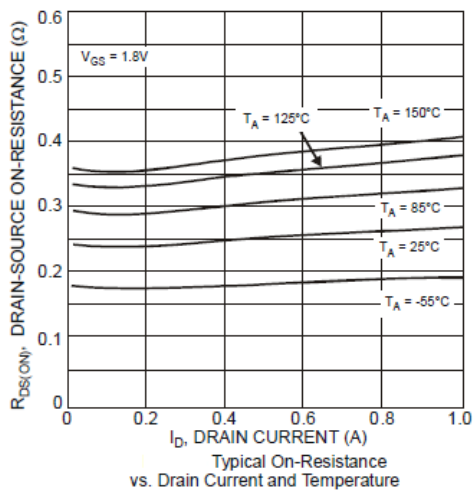
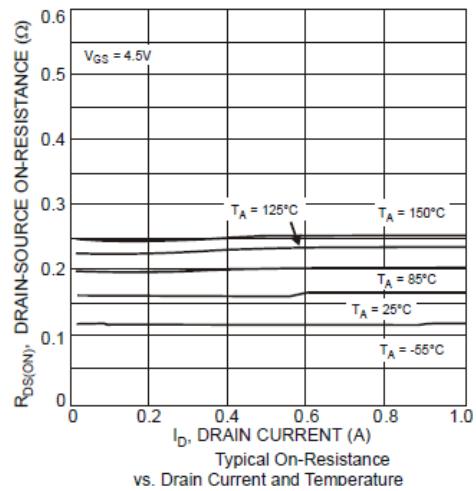
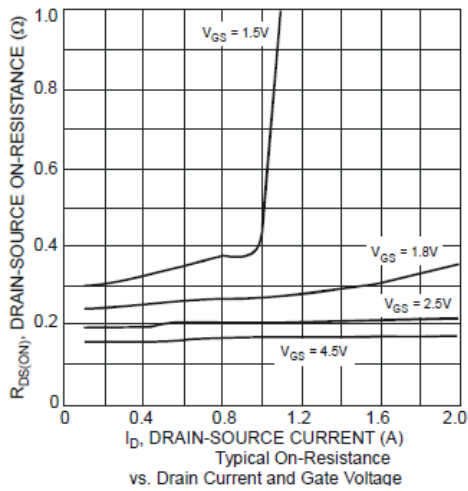
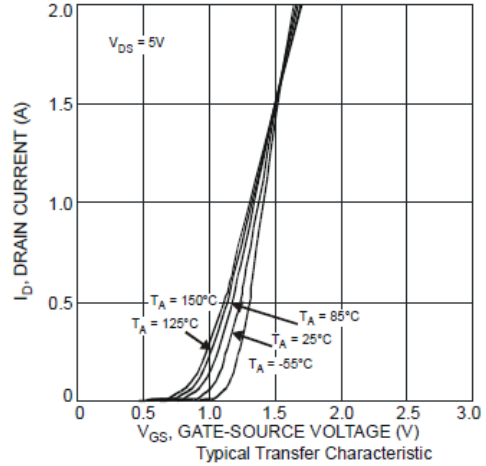
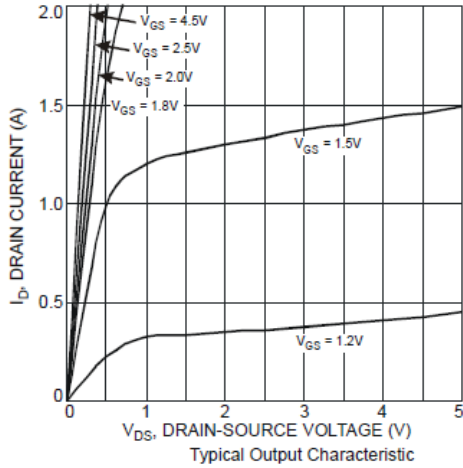
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.3		1.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±1	mA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	uA
		V _{DS} =20V, V _{GS} =0V T _J =85°C			5	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 5V, V _{GS} =4.5V	0.7			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =0.8A		240	360	mΩ
		V _{GS} =2.5V, I _D =0.7A		300	420	
		V _{GS} =1.8V, I _D =0.5A		420	560	
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =0.4A		1		S
Diode Forward Voltage	V _{SD}	I _S =0.15A, V _{GS} =0V		0.65	1.2	V
Dynamic						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V f=1MHz		70		pF
Output Capacitance	C _{oss}			8		
Reverse Transfer Capacitance	C _{rss}			6		
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =4.5V I _D ≅0.6A		1.06	1.38	nC
Gate-Source Charge	Q _{gs}			0.18		
Gate-Drain Charge	Q _{gd}			0.32		
Turn-On Time	t _{d(on)}	V _{DD} =10V, R _L =20Ω I _D ≅0.8A, V _{GEN} =10V R _G =6Ω		5	10	ns
	t _r			5	10	
Turn-Off Time	t _{d(off)}			35	70	
	t _f			15	30	

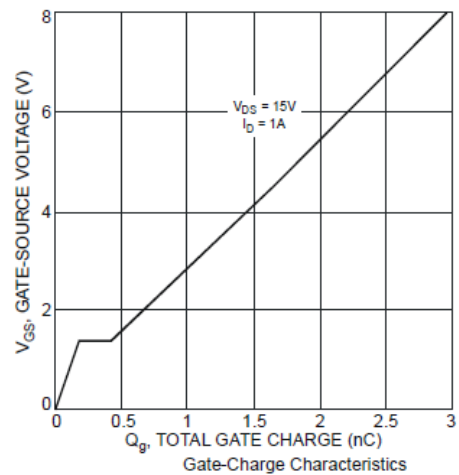
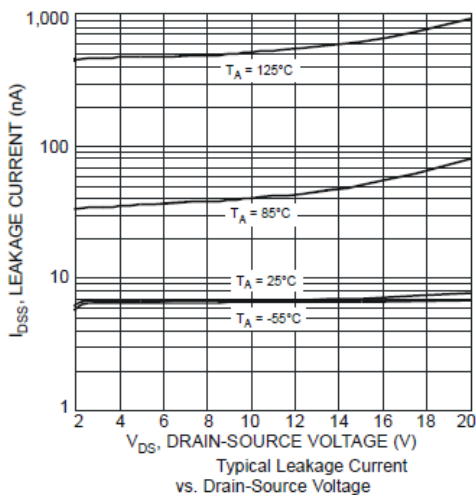
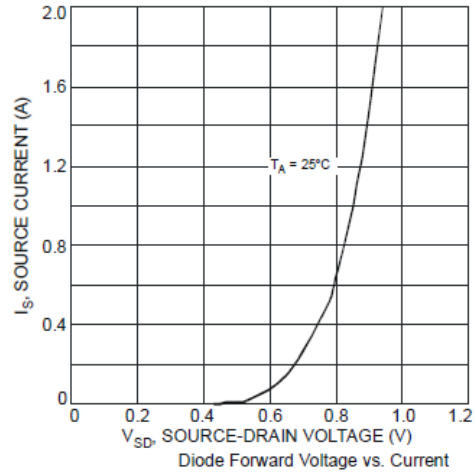
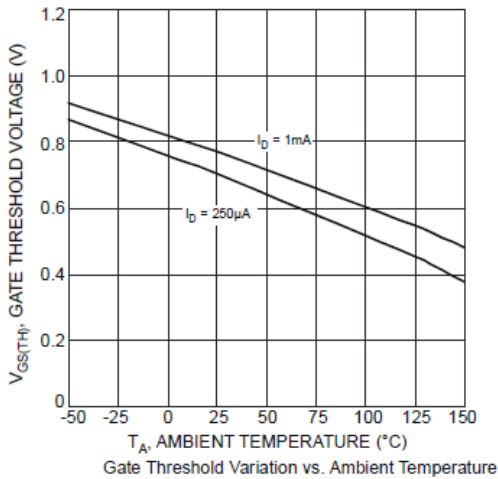
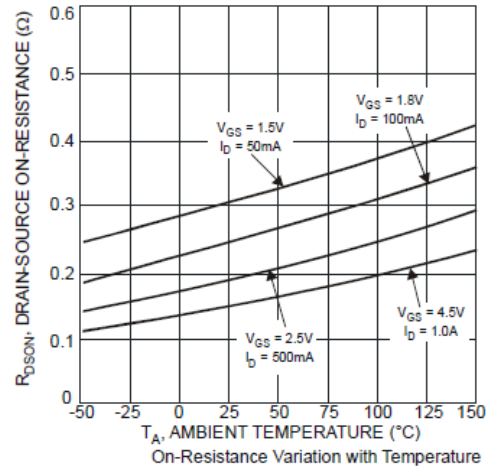
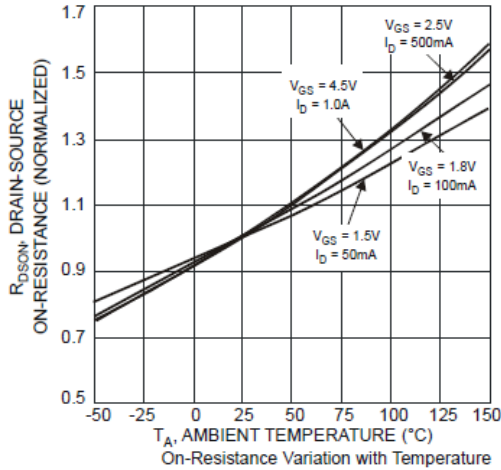


Typical Characteristics





Typical Characteristics





Typical Characteristics

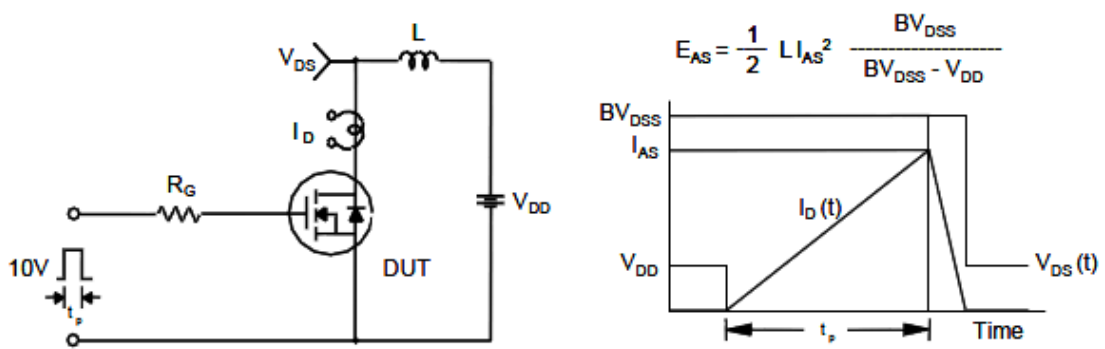
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

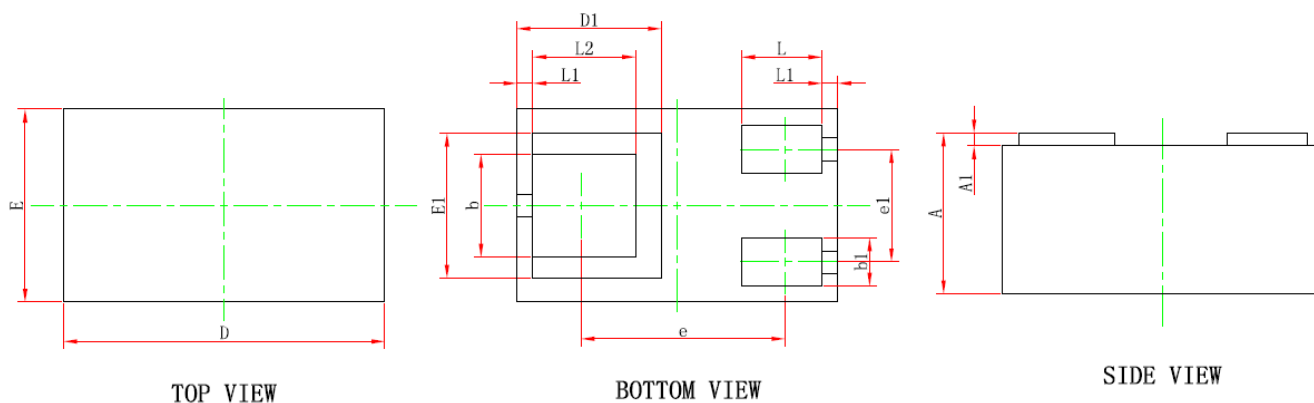


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (DFN1.0X0.6-3L)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.010	0.100	0.000	0.004
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
D1	0.450REF.		0.018REF.	
E1	0.450REF.		0.018REF.	
b	0.270	0.370	0.011	0.015
b1	0.100	0.200	0.004	0.008
e	0.635REF.		0.025REF.	
e1	0.300	0.400	0.012	0.016
L	0.200	0.300	0.008	0.012
L1	0.050REF.		0.002REF.	
L2	0.270	0.370	0.011	0.015

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